



# T1635NZP

## 主要参数 MAIN CHARACTERISTICS

$I_{T(RMS)}$	16A
$V_{DRM}$	800V
$I_{GT}$	20mA

### 用途

- 交流开关
- 相位控制

### APPLICATIONS

- AC switching
- Phase control

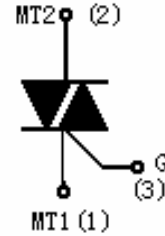
### 产品特性

- 平面工艺芯片，高可靠性和一致性
- 三象限可控硅，触发电流的一致性好
- 环保 RoHS 产品

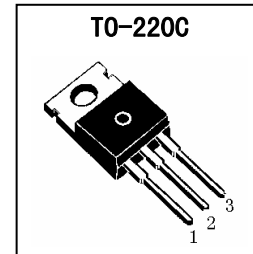
### FEATURES

- The planar process chip for reliability and uniform
- Uniform gate trigger currents in three quadrants
- RoHS products

## 封装 Package



序号 Pin	引线名称 Description
1	主电极 1 MT1
2	主电极 2 MT2
3	门极 G



## 订货信息 ORDER MESSAGES

订货型号 Order codes				印 记 Marking	封 装 Package
有卤-条管	无卤-条管	有卤-编带	无卤-编带		
Halogen-Tube	halogen-Free-Tube	Halogen-Reel	Halogen-Free-Reel	T1635NZP	TO-220C
T1635NZP-C-B	T1635NZP-C-BR	N/A	N/A		



绝对最大额定值 ABSOLUTE RATINGS ( $T_c=25^\circ\text{C}$ )

项 目 Parameter	符 号 Symbol	试 验 条 件 Condition	数 值 Value	单 位 Unit
重复峰值断态电压 Repetitive peak off-state voltage	$V_{\text{DRM}}$		$\pm 800$	V
通态方均根电流 On-state RMS current	$I_{\text{T(RMS)}}$	full sine wave,	16	A
非重复浪涌峰值通态电流 Non-repetitive surge peak on-state current	$I_{\text{TSM}}$	full sine wave ,t=20ms	140	A
		full sine wave ,t=16.7ms	150	A
	$I^2t$	t=10ms	98	$\text{A}^2\text{s}$
通态电流临界上升率 Repetitive rate of rise of on-state current after triggering	$di/dt$	$I_{\text{TM}}=20\text{A}$ , $I_{\text{G}}=0.2\text{A}$ , $di_{\text{G}}/dt=0.2\text{A}/\mu\text{s}$	100	$\text{A}/\mu\text{s}$
峰值门极电流 Peak gate current	$I_{\text{GM}}$		2	A
峰值门极电压 Peak gate voltage	$V_{\text{GM}}$		5	V
峰值门极功率 Peak gate power	$P_{\text{GM}}$		5	W
平均门极功率 Average gate power	$P_{\text{G(AV)}}$	over any 20ms period	0.5	W
存储温度 Storage temperature	$T_{\text{stg}}$		-40~150	$^\circ\text{C}$
操作结温 Operation junction temperature	$T_{\text{VJ}}$		-40~150	$^\circ\text{C}$



电特性 ELECTRICAL CHARACTERISTIC ( $T_c=25^\circ\text{C}$ )

项 目 Parameter	符 号 Symbol	测 试 条 件 Condition	最小 Min	典型 Typ	最大 Max	单位 Unit
峰值重复断态电流 Peak Repetitive Blocking Current	$I_{\text{DRM}}$	$V_{\text{DM}}=V_{\text{DRM}}$ , $T_j=150^\circ\text{C}$ , gate open		--	1.0	mA
峰值通态电压 Peak on-state voltage	$V_{\text{TM}}$	$I_{\text{TM}}=18\text{A}$ , $T_j=25^\circ\text{C}$ ,		--	1.5	V
门极触发电流 Gate trigger current	$I_{\text{GT}}$	$V_{\text{DM}}=12\text{V}$ , $R_L=100\ \Omega$ , MT1(-),MT2(+),G(+)		--	20	mA
		MT1(-),MT2(+),G(-)		--	20	mA
		MT1(+),MT2(-),G(-)		--	20	mA
门极触发电压 Gate trigger voltage	$V_{\text{GT}}$	$V_{\text{DM}}=12\text{V}$ , $R_L=100\ \Omega$ , MT1(-),MT2(+),G(+)		0.7	1.0	V
		MT1(-),MT2(+),G(-)		0.7	1.5	V
		MT1(+),MT2(-),G(-)		0.7	1.5	V
维持电流 Holding current	$I_{\text{H}}$	$V_{\text{DM}}=12\text{V}$ , $I_{\text{GT}}=0.1\text{A}$		--	20	mA
擎住电流 Latching current	$I_{\text{L}}$	$V_{\text{DM}}=12\text{V}$ , $I_{\text{GT}}=0.1\text{A}$ , MT1(-),MT2(+),G(+)		-	30	mA
		MT1(-),MT2(+),G(-)		-	30	mA
		MT1(+),MT2(-),G(-)		-	30	mA
断态临界电压上升率 Rise of off- state voltage	$dV/dt$	$V_{\text{DM}}=67\% V_{\text{DRM(MAX)}}$ , $T_j=150^\circ\text{C}$ , gate open	1000	-	-	V/ $\mu\text{s}$
门极开通时间 Gate controlled turn-on time	tgt	$I_{\text{TM}}=20\text{A}$ , $V_{\text{DM}}=V_{\text{DRM(MAX)}}$ , $I_{\text{G}}=0.1\text{A}$ , $dI_{\text{G}}/dt=5\text{A}/\mu\text{S}$	-	2	-	$\mu\text{s}$

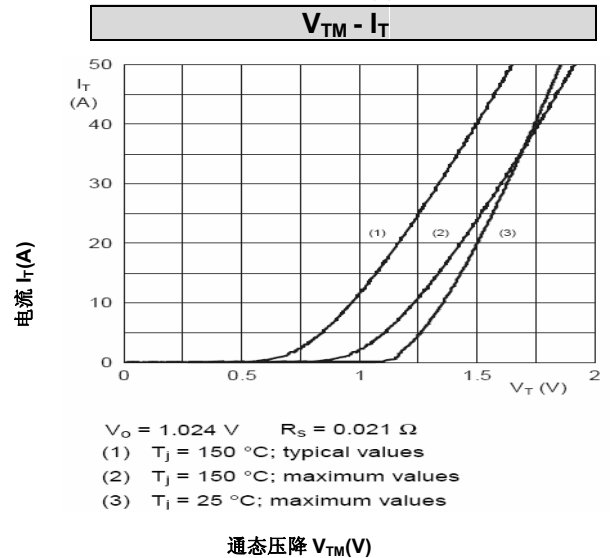
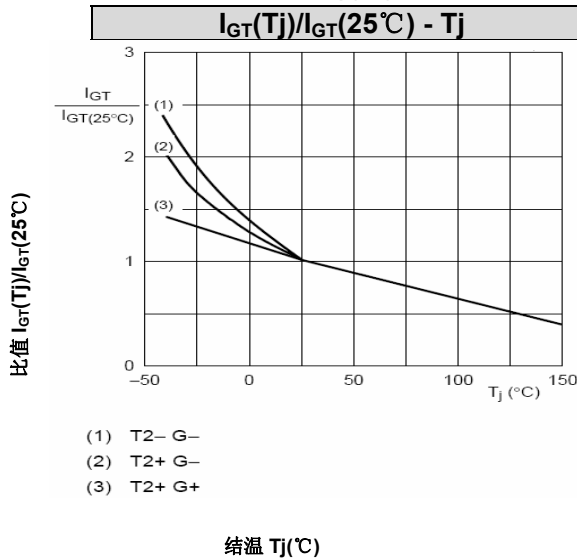
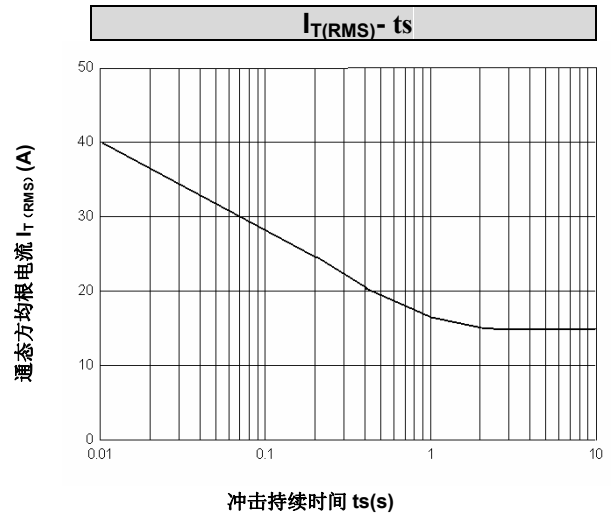
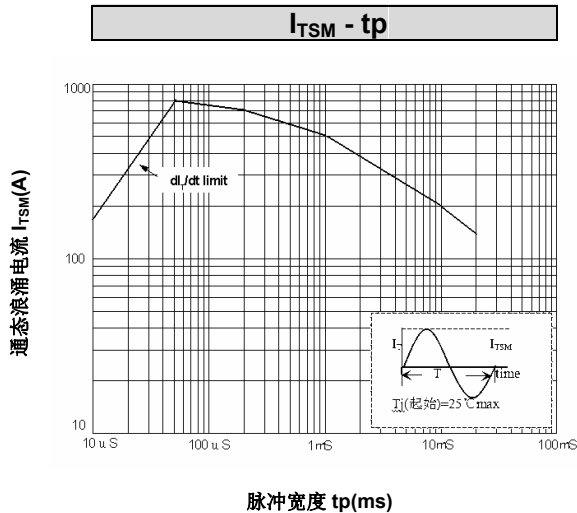
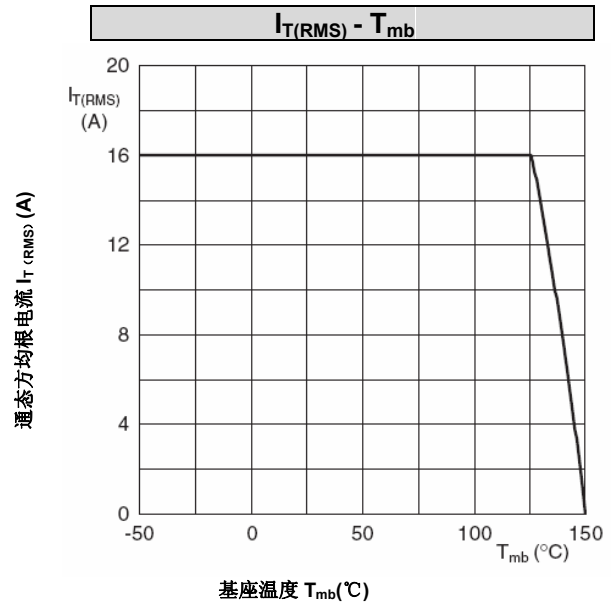
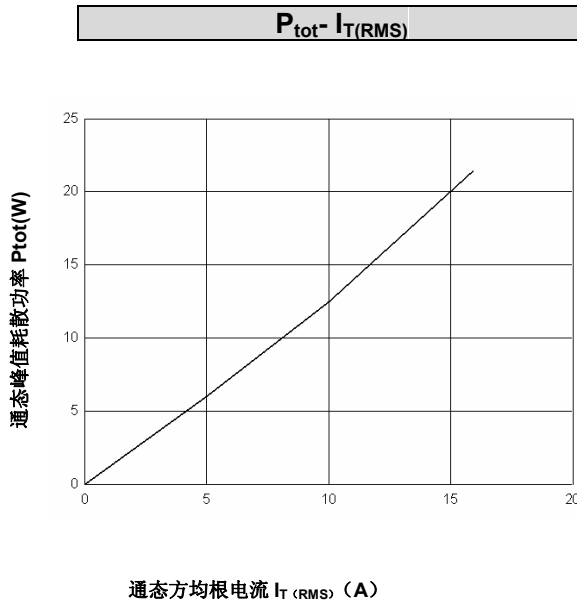
## 热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	条 件 Condition	最小 Min	典型 Typ	最大 Max	单位 Unit
结到安装面的热阻 Thermal resistance junction to mounting base	$R_{\text{th(j-c)}}$	full cycle(TO-220C)			1.2	$^\circ\text{C/W}$





特征曲线 ELECTRICAL CHARACTERISTICS (curves)

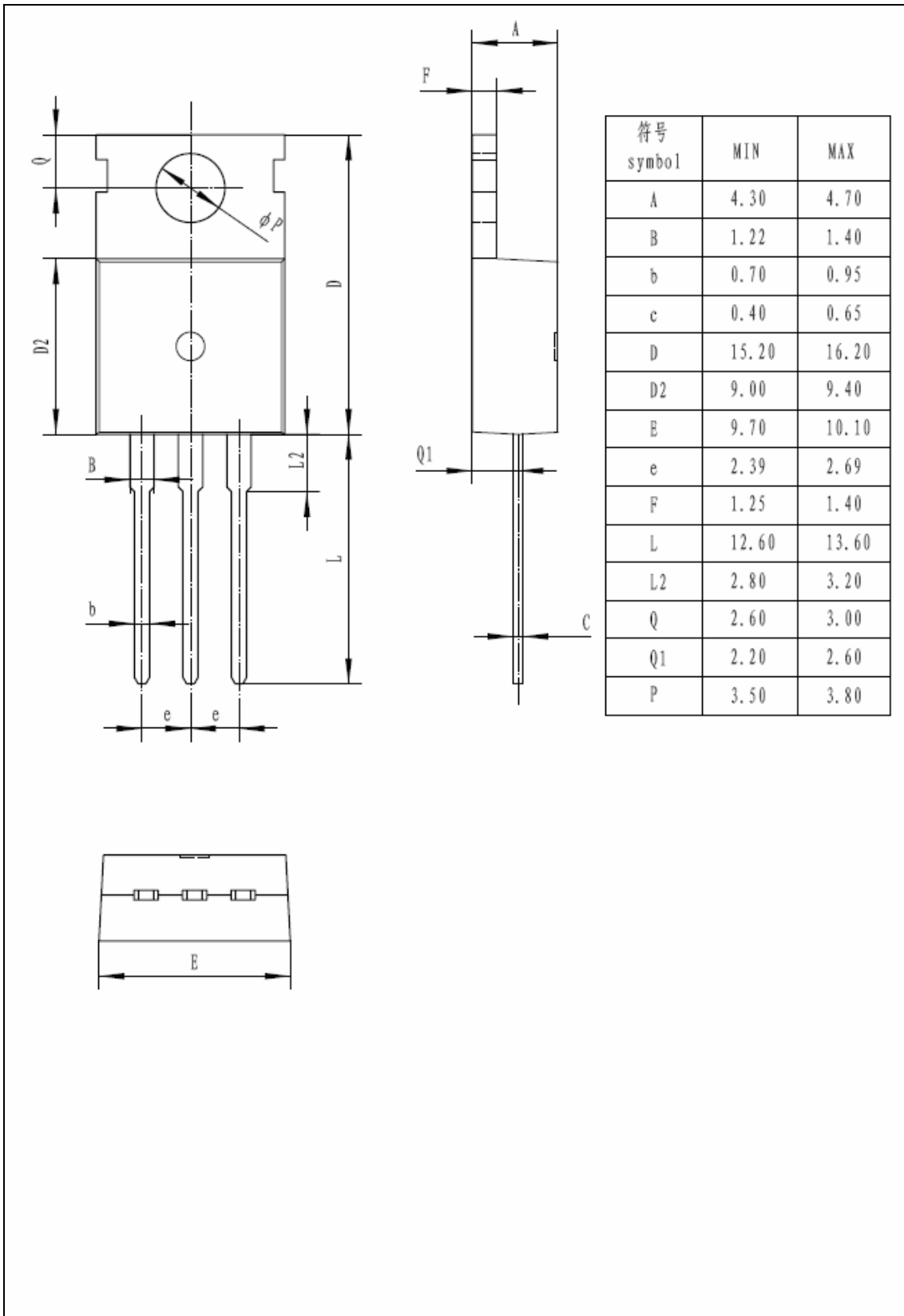




## 外形尺寸 PACKAGE MECHANICAL DATA

TO-220C

单位 Unit : mm



**注意事项**

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3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
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